TYN12B-600LT

SCR

Rev. 01 19 February 2019 Product data sheet

1. General description

Planar passivated Silicon Controlled Rectifier (SCR) in a TO-263 surface mountable plastic package intended for use in applications requiring good bidirectional blocking voltage and high inrush current capability, high thermal cycling performance and high junction temperature capability ($T_{j(max)}$ = 150 °C).

2. Features and benefits

- Good bidirectional blocking voltage capability
- High current surge capability
- High thermal cycling performance
- Surface mountable package
- Planar passivated for voltage ruggedness and reliability
- High junction operating temperature capability ($T_{j(max)}$ = 150 °C)

3. Applications

- Capacitive Discharge Ignition (CDI)
- Crowbar protection
- Inrush protection
- Motor control
- Voltage regulation
- High junction operating temperature capability ($T_{j(max)}$ = 150 °C)

4. Quick reference data

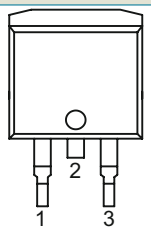
Table 1. Quick reference data

Symbol	Parameter	Conditions	Values	Unit
Absolute maximum rating				
V_{RRM}	repetitive peak reverse voltage		650	V
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 136$ °C; Fig. 1; Fig. 2; Fig. 3	12	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)}$ = 25 °C; t_p = 10 ms; Fig. 4; Fig. 5	120	A
		half sine wave; $T_{j(init)}$ = 25 °C; t_p = 8.3 ms	132	A
T_j	junction temperature		150	°C

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 7		-	-	5	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	20	mA
V_T	on-state voltage	I_T = 12 A; T_j = 25 °C; Fig. 10		-	1.14	1.4	V
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; R_{GK}= 100 Ω; (V_{DM} = 67% of V_{DRM}); exponential waveform;		200	1000	-	V/µs

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode		
2	A	anode		
3	G	gate		
mb	A	mounting base; connect to anode		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
TYN12B-600LT	TO-263	TYN12B-600J	Reel	800	TO-263E	26-May-2017

7. Marking

Table 4. Marking codes

Type number	Marking codes
TYN12B-600LT	TYN12B-600LT

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{DRM}	repetitive peak off-state voltage		650	V
V_{RRM}	repetitive peak reverse voltage		650	V
$I_{T(AV)}$	average on-state current	half sine wave; $T_{mb} \leq 136$ °C;	7.5	A
$I_{T(RMS)}$	RMS on-state current	half sine wave; $T_{mb} \leq 136$ °C; Fig. 1; Fig. 2; Fig. 3	12	A
I_{TSM}	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25$ °C; $t_p = 10$ ms; Fig. 4; Fig. 5	120	A
		half sine wave; $T_{j(init)} = 25$ °C; $t_p = 8.3$ ms	132	A
I^2t	I^2t for fusing	$t_p = 10$ ms; sine wave	72	A^2s
dI_T/dt	rate of rise of on-state current	$I_G = 10$ mA	50	A/µs
I_{GM}	peak gate current		2	A
V_{GM}	peak gate voltage		5	V
P_{GM}	peak gate power		5	W
$P_{G(AV)}$	average gate power	over any 20 ms period	0.5	W
T_{stg}	storage temperature		-40 to 150	°C
T_j	junction temperature		150	°C

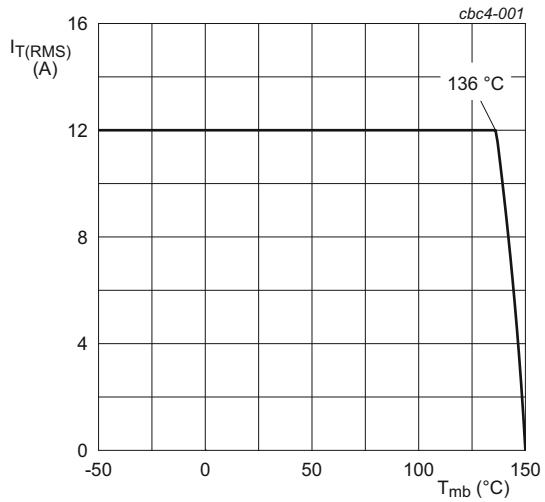
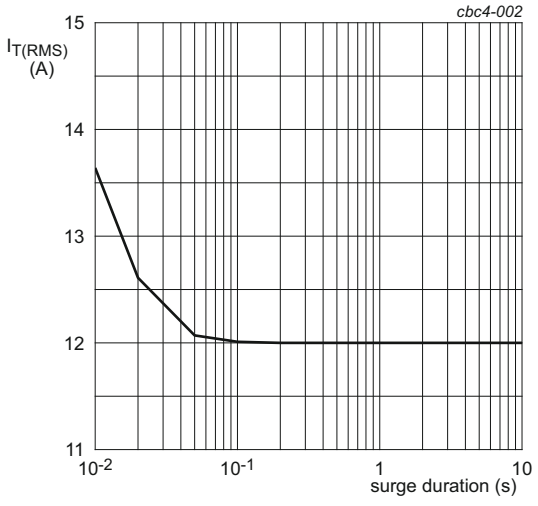
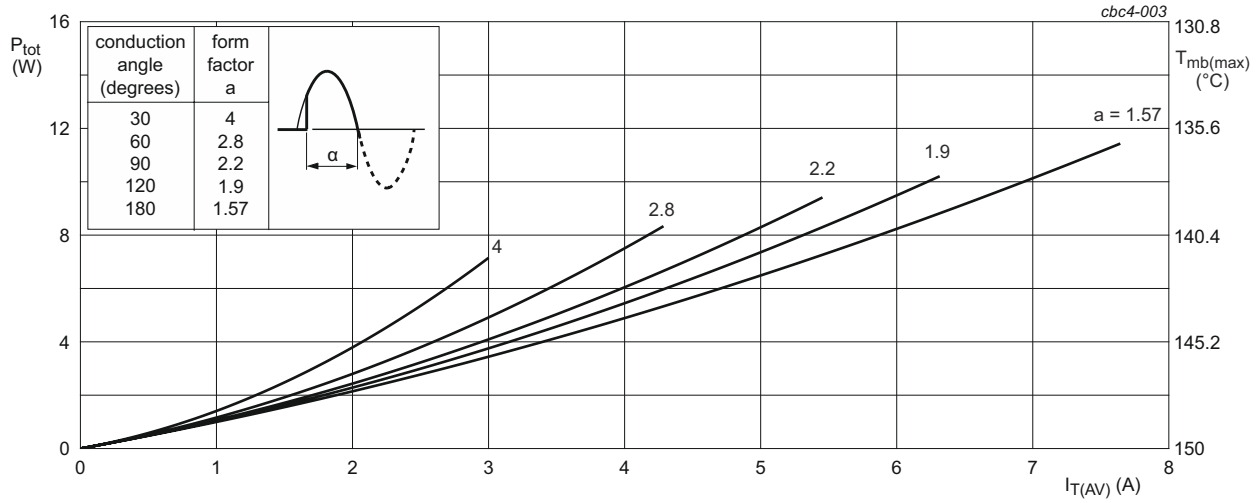


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



f = 50Hz; T_{mb} = 136 °C

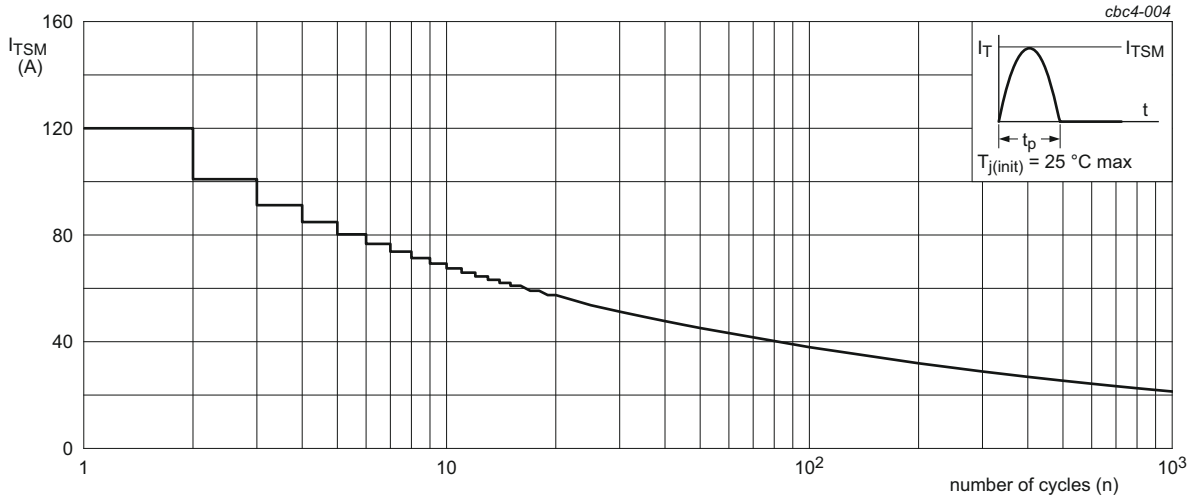
Fig. 2. RMS on-state current as a function of surge duration; maximum values



α = conduction angle

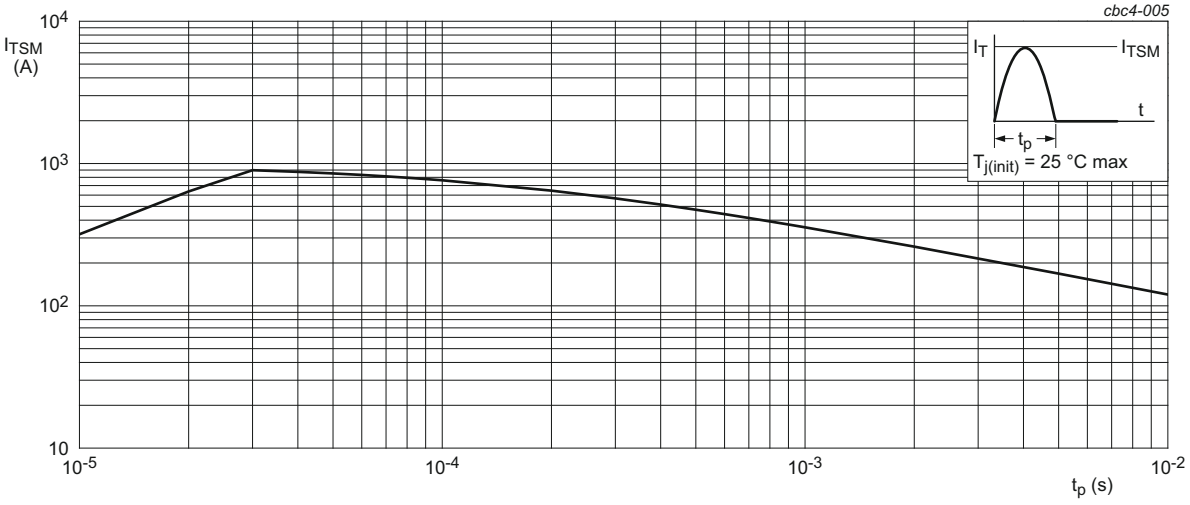
a = form factor = $I_{T(RMS)}$ / $I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values



f = 50 Hz

Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



t_p ≤ 10 ms ;

(1) dI_T/dt limit

Fig. 5. Total power dissipation as a function of RMS on-state current; maximum values

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 6		-	-	1.2	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	minimum footprint, FR4 board		-	55	-	K/W

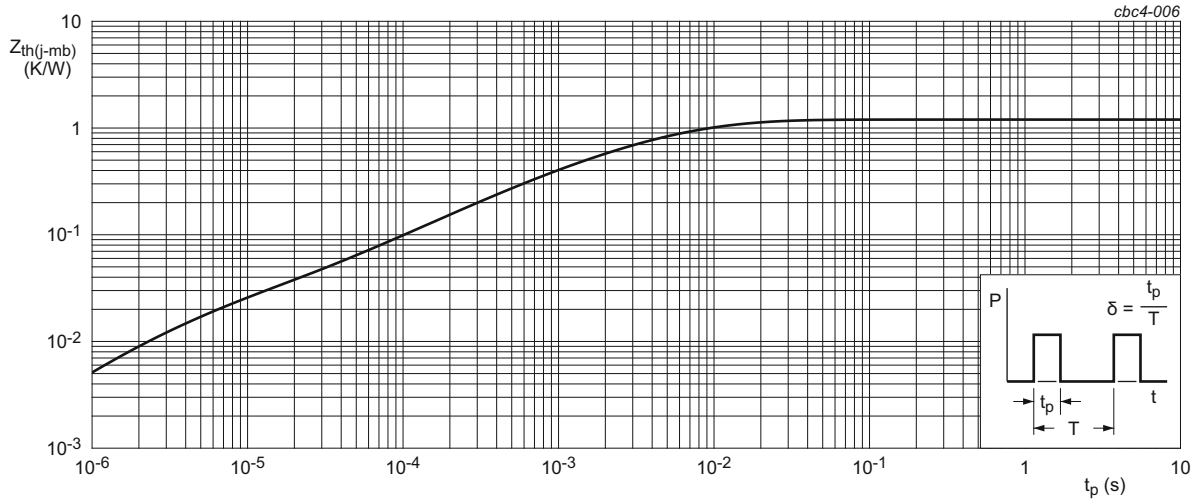


Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
I_{GT}	gate trigger current	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 7		-	-	5	mA
I_L	latching current	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 8		-	-	40	mA
I_H	holding current	V_D = 12 V; T_j = 25 °C; Fig. 9		-	-	20	mA
V_T	on-state voltage	I_T = 12 A; T_j = 25 °C; Fig. 10		-	1.14	1.4	V
V_{GT}	gate trigger voltage	V_D = 12 V; I_T = 0.1 A; T_j = 25 °C; Fig. 11		-	0.7	1	V
		V_D = 400 V; I_T = 0.1 A; T_j = 150 °C; Fig. 11		0.25	0.4	-	V
I_D	off-state current	V_D = 650 V; T_j = 150 °C		-	-	1	mA
I_R	reverse current	V_D = 650 V; T_j = 150 °C		-	-	1	mA
Dynamic characteristics							
dV_D/dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 150 °C; R_{GK} = 100 Ω; (V_{DM} = 67% of V_{DRM}); exponential waveform;		200	1000	-	V/µs
		V_{DM} = 402 V; T_j = 150 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit		50	-	-	V/µs
t_{gt}	gate-controlled turn-on time	I_{TM} = 12 A; V_D = 600 V; I_G = 10 mA; $(dI_G/dt)_M$ = 5 A/µs; T_j = 25 °C			2	-	µs
t_q	commutated turn-off time	V_{DM} = 402 V; T_j = 150 °C; I_{TM} = 12 A; V_R = 25 V; dV_D/dt = 30 V/µs; $(dI_T/dt)_M$ = 30 A/µs; $R_{GK(ext)}$ = 100 Ω ; (V_{DM} = 67% of V_{DRM})			70	-	µs

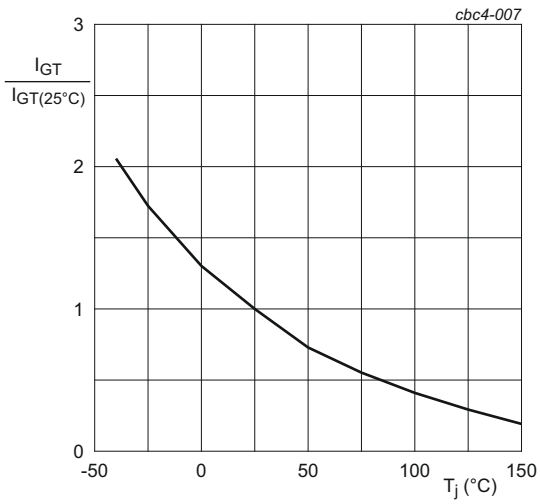


Fig. 7. Normalized gate trigger current as a function of junction temperature

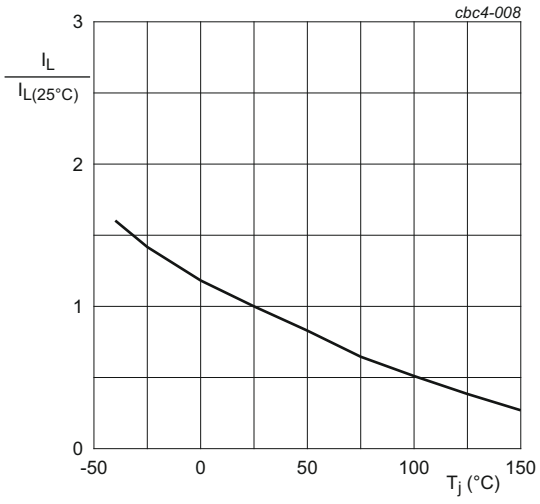


Fig. 8. Normalized latching current as a function of junction temperature

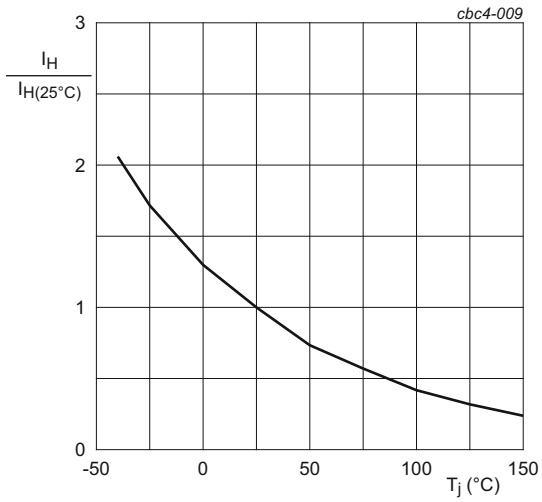
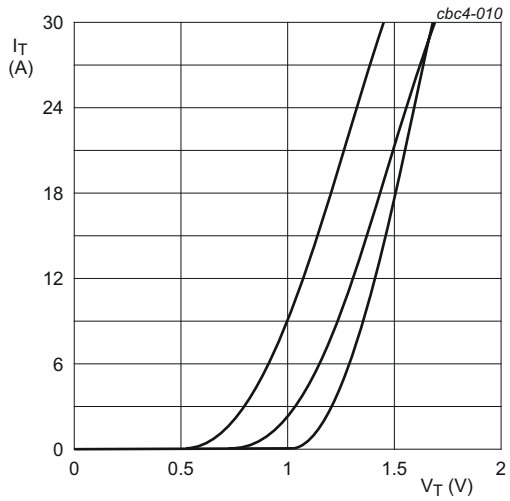


Fig. 9. Normalized holding current as a function of junction temperature



V_o = 0.922 V; R_s = 0.0304 Ω
(1) T_j = 150 °C; typical values
(2) T_j = 150 °C; maximum values
(3) T_j = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

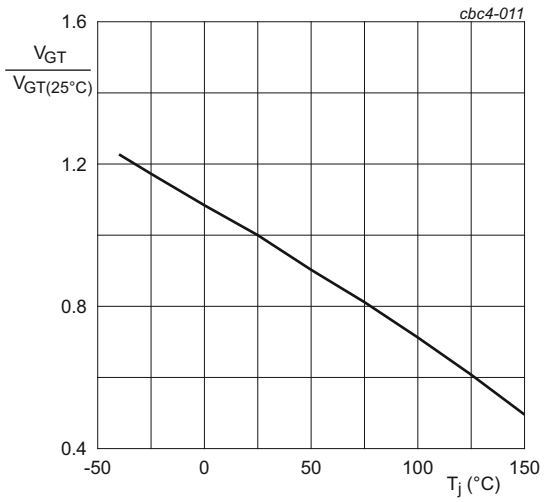
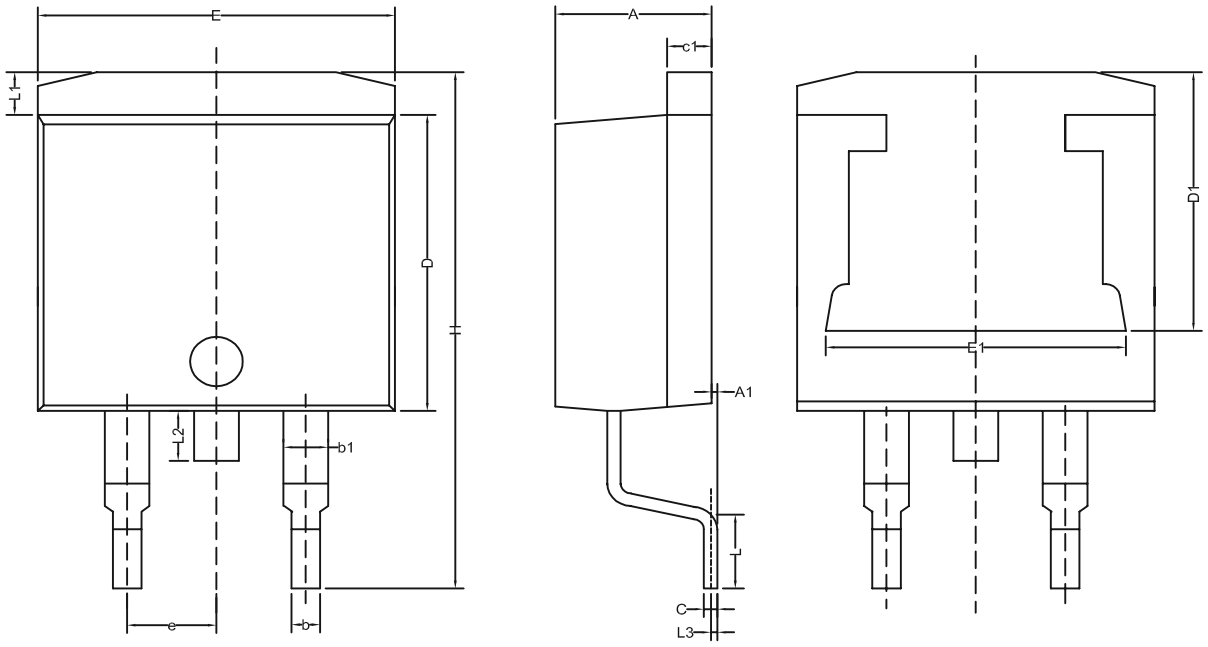
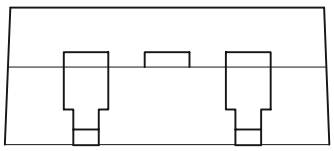


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) TO263





Unit		A	A1	b	b1	c	c1	D	D1	E	E1	e	H	L	L1	L2	L3
MM	min	4.35	0.00	0.69	1.14	0.38	1.14	8.50	7.50	10.00	8.25	2.54 (BSC)	14.60	2.50	1.00	1.27	0.25 (BSC.)
	max	4.75	0.15	0.99	1.73	0.61	1.40	9.02	8.00	10.40	8.80		15.60	2.79	1.65	1.78	

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Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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13. Contents

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